

Silicon PNP Power Transistors

2N6124 2N6125 2N6126

DESCRIPTION

- With TO-220 package
- Complement to PNP type :
2N6121 ;2N6122 ;2N6123

APPLICATIONS

- For use in power amplifier and switching circuit applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

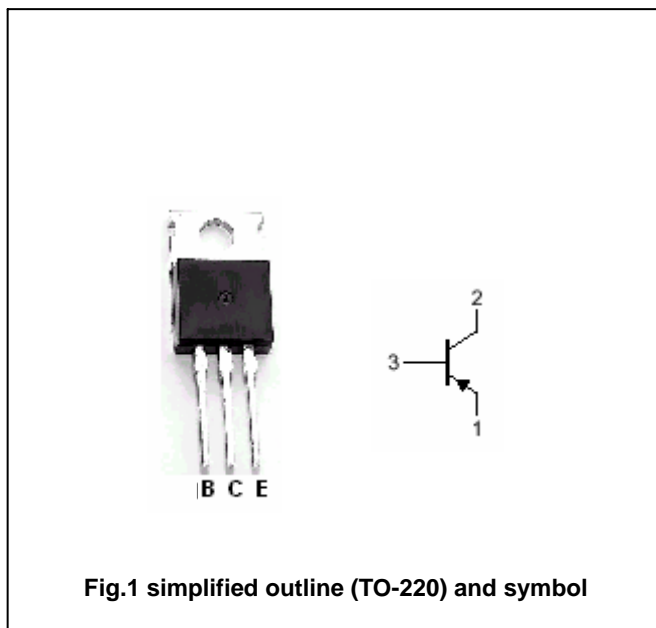


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6124	-45	V
		2N6125	-60	
		2N6126	-80	
V _{CEO}	Collector-emitter voltage	2N6124	-45	V
		2N6125	-60	
		2N6126	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-8	A
I _B	Base current		-1	A
P _T	Total power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	3.125	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6124	I _C =-0.1A ; I _B =0	-45			V	
		2N6125		-60				
		2N6126		-80				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-0.6	V		
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-4.0A; I _B =-1.0A			-1.4	V		
V _{BE(on)}	Base-emitter on voltage	I _C =-1.5A ; V _{CE} =-2V			-1.2	V		
I _{CEx}	Collector cut-off current	2N6124	V _{CE} =-45V; V _{BE} =1.5V T _C =125			-0.1 -2.0	mA	
		2N6125		V _{CE} =-60V; V _{BE} =1.5V T _C =125				-0.1 -2.0
		2N6126		V _{CE} =-80V; V _{BE} =1.5V T _C =125				-0.1 -2.0
I _{CEO}	Collector cut-off current	2N6124	V _{CE} =-45V; I _B =0				mA	
		2N6125		V _{CE} =-60V; I _B =0				-1.0
		2N6126		V _{CE} =-80V; I _B =0				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA		
h _{FE-1}	DC current gain	2N6124	I _C =-1.5A ; V _{CE} =-2V	25		100		
		2N6125				80		
		2N6126						
h _{FE-2}	DC current gain	2N6124	I _C =-4A ; V _{CE} =-2V	10				
		2N6125						
		2N6126				7		
f _T	Transition frequency	I _C =-1A ; V _{CE} =-4V	2.5			MHz		

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)